

STZ150NF55T

N-CHANNEL TEMPERATURE SENSING 55V - P2PAK SAFeFET™ MOSFET

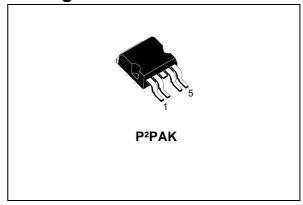
DATA BRIEF

General features

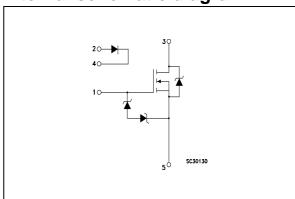
| Туре | V _{DSSS} | R _{DS(on)} | I _D |
|-------------|-------------------|---------------------|----------------|
| STZ150NF55T | 55 V | $<$ 9 m Ω | 40 A(1) |

- INTEGRATED ESD PROTECTION
- INTEGRATED TEMPERATURE SENSING
- STANDARD VGS(th) LEVEL
- 175°C JUNCTION TEMPERATURE

Package



Internal schematic diagram



Applications

■ HIGH CURRENT SWITCHING

Order codes

| Sales Type | Marking | Package | Packaging |
|-------------|-----------------------|---------|-------------|
| STZ150NF55T | STZ150NF55T Z150NF55T | | TAPE & REEL |

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1 Absolute maximum ratings

Table 1. Absolute maximum ratings

| Symbol | Parameter | Value | Unit |
|------------------------------------|--|------------|------|
| V _{DS} | Drain-Source Voltage (V _{GS} = 0) | 55 | V |
| V _{GS} | Gate-Source Voltage ± 18 | | V |
| I _D Note 1 | Drain Current (continuous) at T _C = 25°C 40 | | Α |
| I _D Note 1 | Drain Current (continuous) at T _C = 100°C | 40 | Α |
| I _{DM} | Drain Current (pulsed) | 160 | Α |
| P _{TOT} | Total Dissipation at T _C = 25°C | 250 | W |
| | Derating Factor | 1.67 | W/°C |
| Vesd(G-S) | G-S ESD (HBM C=100pF, R=1.5kΩ) | >4 | kV |
| E _{AS} | Single Pulse Avalanche Energy | TBD | mJ |
| T _j T _{stg} | Operating Junction Temperature Storage Temperature | -55 to 175 | °C |

STZ150NF55T 2 Electrical characteristics

2 Electrical characteristics

(T_{CASE} = 25 °C unless otherwise specified)

Table 2. On/Off

| Symbol | Parameter | Test Conditions | Min. | Тур. | Max. | Unit |
|----------------------|--|---|------|------|------|------|
| V _{(BR)DSS} | Drain-Source Breakdown Voltage | I _D = 250μA, V _{GS} = 0 | 55 | | | V |
| I _{DSS} | Zero Gate Voltage Drain Current (V _{GS} = 0) | V _{DS} = Max Rating, | | | 10 | μΑ |
| I _{GSS} | Gate Body Leakage Current (V _{DS} = 0) | $V_{GS} = \pm 15V, V_{DS} = 0$ | | | 10 | μΑ |
| V _{GS(th)} | Gate Threshold Voltage | $V_{DS} = V_{GS}, I_{D} = 250 \mu A$ | 2 | | 4 | V |
| R _{DS(on)} | Static Drain-Source On Resistance | V _{GS} = 10 V, I _D = 20 A | | | 9 | mΩ |
| V _F | Temperature Sense diode forward voltage | I _f =250μΑ | | 3.5 | | V |

⁽¹⁾ Limited by wire bonding



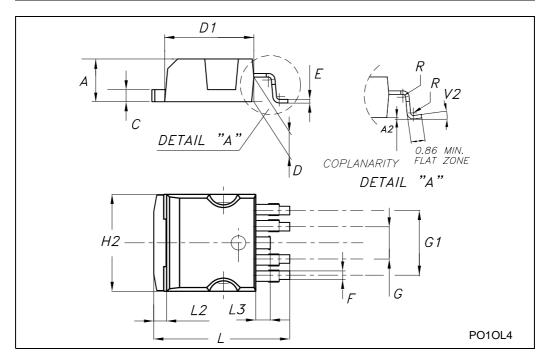
3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com



PENTAWATT SMD (P2PAK) MECHANICAL DATA

| DIM. | mm | | | inch | | | |
|-------|-------|------|-------|-------|------|-------|--|
| DINI. | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. | |
| А | 4.30 | | 4.80 | 0.169 | | 0.188 | |
| A2 | 0.03 | | 0.23 | 0.001 | | 0.009 | |
| С | 1.17 | | 1.37 | 0.046 | | 0.053 | |
| D | 2.40 | | 2.80 | 0.094 | | 0.110 | |
| D1 | 8.95 | | 9.35 | 0.352 | | 0.368 | |
| E | 0.35 | | 0.55 | 0.013 | | 0.021 | |
| F | 0.80 | | 1.05 | 0.031 | | 0.041 | |
| G | 3.20 | | 3.60 | 0.125 | | 0.141 | |
| G1 | 6.60 | | 7.00 | 0.259 | | 0.275 | |
| H2 | | | 10.40 | | | 0.409 | |
| L | 13.59 | | 14.39 | 0.535 | | 0.566 | |
| L2 | 1.27 | | 1.40 | 0.05 | | 0.055 | |
| L3 | 1.30 | | 1.70 | 0.051 | | 0.066 | |
| R | | 0.30 | | | | | |
| V2 | 0 d | | 8 d | | | | |



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4 Revision History STZ150NF55T

4 Revision History

| Date | Revision | Changes |
|-------------|----------|------------------|
| 22-Jul-2005 | 1 | Initial release. |



STZ150NF55T 4 Revision History

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